

Description

The present invention relates to a video signal processing circuit, and more particularly to a burst gate pulse generating circuit for generating a burst gate pulse for extracting a burst signal from a sync separation output signal.

Generally, a burst gate pulse generating circuit is used in a color television set, a video tape recorder, and the like. A sync separation signal is supplied to a burst gate pulse generating circuit which in turn generates a burst gate pulse. The burst gate pulse derived from the burst gate pulse generating circuit is used as a gate pulse for the burst signal detection in a color synchronizing circuit. The same is also used in an AGC (automatic gain control) circuit, as a key pulse for AGC detection. Specifically, in the AGC circuit, a potential of the video signal at the pedestal portion is extracted by using the burst gate pulse. This potential at the pedestal portion is compared with a reference potential. By using the comparison result, the gain of the AGC circuit is controlled so that the amplitude of the sync signal is kept constant. The burst gate pulse is used as a reference signal in the ACC (automatic color control) detection mode. See for example US-A-3 949 418 and GB-A-2 146 199

As just mentioned, the burst gate pulse is used as reference signals in the video circuits. Therefore, high exactness is required for the pulse width and the pulse position of the burst gate pulse. Actually, however, noise is frequently introduced into the sync separation signal. The introduced noise leads to improper operation of the burst gate pulse generating circuit, and consequently generation of a mistaken burst gate pulse.

An example of a conventional burst gate pulse generating circuit is illustrated in Fig. 1. In the figure, reference symbol IN indicates an input terminal for receiving a sync separation circuit; OUT an output terminal for outputting a burst gate pulse; Q1 to Q16, npn or pnp transistors; R1 to R13, resistors; C1 a capacitor; V1 and V2 constant voltage sources; I1 and I2 constant current sources; and A1 to A3, differential amplifiers. A value of the constant voltage source V2 is higher than that of the constant voltage source V1.

Fig. 2 shows a timing chart useful in explaining the operation of the burst gate pulse generating circuit shown in Fig. 1. In Fig. 2, a waveform A represents a variation of a sync separation signal applied to the input terminal IN; a waveform B, a voltage variation of a base signal of each of the transistors Q2, Q8 and Q15; a waveform C, a voltage variation of a base signal of each of the transistors Q4 and Q7 or a current variation of at the collector of each of the transistors Q5 and Q6; a waveform D, a voltage variation of a base signal

of the transistor Q3; and a waveform E, a variation of a burst gate pulse derived from the output terminal OUT.

The operation of the above burst gate pulse generating circuit will be described in brief. When a sync signal rises to "1" level, charge to the capacitor C1 starts and it is charged by the power source voltage V_{CC} via the resistor R3. With progression of the charging operation, a base voltage of the transistor Q3 rises at a given time constant as indicated by the waveform D in Fig. 2. The base voltage of the transistor Q3 exceeds a voltage V_0 that is obtained by dividing the power source voltage V_{CC} by the resistors R4, R7 and R6. At this time, the transistor Q3 is turned on, while the transistor Q4 is turned off. In turn, the transistors Q5, Q6 and Q7 are also turned off. The turning off of the transistor Q7 places the bases of the transistors Q2, Q8 and Q15 in a "1" level, as indicated by the waveform B.

When the base voltage of the transistor Q3 rises and exceeds the voltage of the constant voltage source V1, the transistor Q14 is turned on and a signal at the output terminal OUT rises to a level of "1". See the waveform E in Fig. 2. The base voltage of the transistor Q3 further rises and exceeds the value of the constant voltage source V2. The transistor Q9 is turned off, and the signal at the output terminal OUT drops again to "0", as indicated by the waveform E.

In this way, in the conventional burst gate pulse generating circuit, a pulse signal with a predetermined pulse width is generated in synchronism with the leading edge of the pulse contained in the sync separation signal.

Also in response to the noise contained in the sync separation signal, the burst gate pulse generating circuit operates to generate pulses in a similar way.

Accordingly, an object of the present invention is to provide a burst pulse generating circuit which is free from an improper operation due to the noise mixed into an input signal.

According to the present invention, there is provided a burst gate pulse generating circuit comprising: first circuit means for generating a first voltage increasing at a predetermined time constant in synchronism with the leading edge of a pulse contained in a sync signal applied thereto; second circuit means for stopping the first voltage generating operation by said first circuit means when the trailing edge of said pulse contained in said sync signal arrives at said first circuit means before said first voltage reaches a fixed second voltage; and third circuit means for generating a train of burst gate pulses through the comparison of said first voltage derived from said first circuit means with fixed second and third voltages which

are larger than said second voltage, and different from each other.

This invention can be more fully understood from the following detailed description when taken in conjunction with the accompanying drawings, in which:

Fig. 1 is a circuit diagram of a conventional burst gate pulse generating circuit;

Fig. 2 shows a timing chart useful in explaining the operation of the Fig. 1 circuit;

Fig. 3 is a circuit diagram of a burst gate pulse generating circuit according to an embodiment of the present invention; and

Fig. 4 shows a timing chart useful in explaining the operation of the Fig. 3 circuit.

Reference is made to Fig. 3 showing a burst gate pulse generating circuit according to an embodiment of the present invention.

In the figure, the base of an npn transistor Q1 is coupled through a resistor R1 with an input terminal IN that is coupled for reception with a sync separation signal. The same base is also connected through a resistor R2 to a ground potential V_{SS} . The emitter of the transistor Q1 is connected to the ground potential V_{SS} , and the collector thereof is connected to a power source potential V_{CC} through a constant current source I1. The same collector is further connected to the base of an npn transistor Q2. The transistor Q2 is connected at the emitter to the ground potential V_{SS} , and at the collector to the power source potential V_{CC} via a resistor R3. The collector of the transistor Q2 is further connected to the ground potential V_{SS} via a capacitor C1, and to the base of an npn transistor Q3. These transistors Q1 and Q2, resistors R1 to R3, a capacitor C1 and constant current source I1 make up a first circuit 10.

The collector of the transistor Q3 is coupled with the power source potential V_{CC} via a resistor R4, and the emitter thereof is connected to the ground potential V_{SS} via a resistor R5. The emitter of the same transistor is also connected to the emitter of an npn transistor Q4. The transistors Q3 and Q4 whose emitters are interconnected make up a first differential amplifier A1. The base of the transistor Q4 is connected through a resistor R6 to the ground potential V_{SS} , and through a resistor R7 to the collector of the transistor Q3.

The collector of the transistor Q4 is connected to the collector and the base of a pnp transistor Q5. The emitter of the transistor Q5 is connected through a resistor R8 to the power source potential V_{CC} . The base of the transistor Q5 is connected to the base of a pnp transistor Q6. The emitter of the transistor Q6 is connected through a resistor R9 to the power source potential V_{CC} , and the collector thereof is connected through a resistor R10 to the ground potential V_{SS} and to the base of the transis-

tor Q7. The emitter of the transistor Q7 is coupled with the ground potential V_{SS} , and the collector thereof is connected to the base of an npn transistor Q8. The emitter of the transistor Q8 is coupled with the ground potential V_{SS} , and the collector thereof is connected to the base of the transistor Q4.

The collector of the transistor Q2 is connected to the base of an npn transistor Q9. The collector of the transistor Q9 is connected to the power source potential V_{CC} , and the emitter thereof is connected to the emitter of an npn transistor Q10. The transistor Q9 and the transistor Q10 whose emitters are interconnected make up a second differential amplifier A2. The emitters of these transistors Q9 and Q10 are connected through a constant current source I2 to the ground potential V_{SS} . The base of the transistor Q10 is connected to the ground potential V_{SS} via a constant voltage source V2. The collector of the transistor Q10 is connected to the collector and the base of a pnp transistor Q11. The emitter of the transistor Q11 is connected through a resistor R11 to the power source potential V_{CC} . The base of the transistor Q11 is connected to the base of a pnp transistor Q12. The emitter of the transistor Q12 is connected to the power source potential V_{CC} by way of a resistor R12. The collector thereof is connected to the collectors of transistors Q13 and Q14 of the pnp type. The transistors Q13 and Q14 cooperate to form a third differential amplifier A3. The base of the transistor Q13 is connected to the collector of the transistor Q2, and collector thereof is coupled with the ground potential V_{SS} . The base of the transistor Q14 is connected through a constant voltage source V1 to the ground potential V_{SS} . The collector of the transistor Q14 is connected to the collector of an npn transistor Q15, and an output terminal OUT from which a stream of a burst gate pulse is produced. The collector of the transistor Q14 is connected through a resistor R13 to the ground potential V_{SS} . The emitter of the transistor Q15 is connected to the ground potential V_{SS} , and its base is connected to the collector of the transistor Q1. The base of an npn transistor Q16 is connected to the input terminal IN, and its collector is connected to the power source potential V_{CC} . The emitter of the transistor Q16 is connected to the emitters of the transistors Q9 and Q10 that are connected together.

Base of an npn transistor Q17 is connected through a resistor R16 to the input terminal IN. The emitter of this transistor Q17 is connected through a resistor R17 to the ground potential V_{SS} , and its collector is connected to the base of an npn transistor Q18 and the collector of a pnp transistor Q19. The collector of the transistor Q17 is connected to the ground potential V_{SS} via a resistor

R14. The collector of the transistor Q18 is connected to the base of the transistor Q7, and its emitter is connected to the ground potential V_{SS} . The base of the transistor Q19 is connected to the collector of the transistor Q2, and its emitter is connected to the emitter of a pnp transistor Q20. The transistors Q19 and Q20 that are interconnected at the emitters make up a fourth differential amplifier A4. The collector of the transistor Q20 is connected to the ground potential V_{SS} , and its base is connected through a constant voltage source V3 to the ground potential V_{SS} . The emitters of the transistors Q19 and Q20 are connected together and to the collector of a pnp transistor Q21. The transistors Q21 and Q5 are interconnected at the bases. The emitter of the transistor Q21 is connected through a resistor R15 to the power source potential V_{CC} .

The differential amplifiers A1 and A4, transistors Q5 to Q8, Q17 to Q20, resistors R4 to R10, R14 to R17, and constant voltage source V3 cooperate to form a second circuit 20. The differential amplifiers A2 and A3, transistors Q11, Q12 and Q15, resistors R11, R12 and R13, constant voltage sources V1 and V2, and constant current source I2 cooperate to form a third circuit 30.

In the above circuit arrangement, a voltage of the constant current source V3 is smaller than those of the constant voltage source V1 and V2.

Fig. 4 shows a timing chart useful in explaining the operation of the burst gate pulse generating circuit shown in Fig. 3. In Fig. 4, a waveform A represents a variation of a sync separation signal applied to the input terminal IN; a waveform B, a voltage variation of a base signal of each of the transistors Q2, Q8 and Q15; a waveform C, a voltage variation of a base signal each of the transistors Q4 and Q7 or a current variation at the collector terminal of each of the transistors Q5 and Q6; a waveform D, a voltage variation of a base signal of the transistor Q18; and a waveform E, a variation of a base voltage of the transistor Q3; a waveform F, a voltage variation of a signal derived from the output terminal OUT.

When an input signal is absent, viz., no sync separation signal is in a "0" level, the transistor Q1 is turned off. Under this condition, the burst gate pulse generating circuit will operate in either of the following two modes. In a first mode, the transistor Q8 is turned on. In a second mode, a voltage V_0 , that is obtained by dividing the power source voltage V_{CC} by the resistors R4, R7 and R6 and is given by a relation (1), is applied to the base of the transistor Q4 before the transistor Q8 is turned on. The transistor is turned on, the transistors Q5, Q6, and Q7 are turned on, and finally the transistor Q8 is turned off.

$$V_0 = \{R7 + R6\} / \{R4 + R7 + R6\} \times V_{CC} \quad (1)$$

In the first mode, the transistor Q1 is turned off, the transistors Q2 and Q8 are turned on, and the transistors Q3, Q4, Q5, Q6 and Q7 are turned off. The transistors Q16 and Q9 are turned off, the transistors Q10, Q11, Q12, Q13 are turned on, and the transistors Q14 and Q15 are turned off. Accordingly, the signal at the output terminal OUT becomes "0" in level, as indicated by the waveform F in Fig. 4. In the second mode, the transistor Q1 is turned off, the transistors Q4, Q5, Q6, and Q7 are turned on, and the transistors Q2 and Q8 are turned off. Upon turning off the transistor Q2, the power source potential V_{CC} starts to charge the capacitor C1 through the resistor R3. When the base potential of the transistor Q3 increases to exceed the voltage V_0 as given by the relation (1), the transistor Q3 is turned on, so that the transistors Q4 to Q7 are turned off. Then, the transistor Q2 and Q8 are turned on. This state is the same as that in the first mode. Also in the second state, the signal at the output terminal OUT becomes "0" in level as indicated by the waveform F in Fig. 4.

When the sync separation signal rises to "1" level, the transistor Q1 is turned on. The transistors Q2, Q8 and Q15 are cut off. At this time, the base voltage of the transistor Q4 is set to V_0 and transistor Q2 is turned off, so that charge to the capacitor C1 starts through the resistor R3 at a time constant as defined by the values of the capacitor C1 and the resistor R3. The base voltage of the transistor Q3 rises as indicated by the waveform E. Until the base voltage exceeds the voltage V_0 , the transistor Q3 remains cut off, while the transistor Q4 remains turned on. The result is that the transistors Q5, Q6, and Q7 are in an on state and the transistors Q2, Q8 and Q15 are left in an off state.

When the sync separation signal is pulsed from "1" to "0", the transistor Q1 is turned off. At this time, the transistors Q4, Q5, Q6, and Q7 maintain an on state, while the transistors Q2, Q8 and Q15 maintain a cut-off state. The transistors Q10 to Q13 are in an on state. The charge to the capacitor C1 is performed. When the base voltage of the transistor Q13 exceeds the constant voltage V1, the transistor Q14 is turned on and the voltage at the output terminal OUT rises to "1" as indicated by the waveform F in Fig. 4. The charge to the capacitor C1 is successfully performed, and the transistor Q10 is cut off. Accordingly, the transistors Q11 and Q12 are cut off, and the current supply to the transistors Q13 and Q14 is stopped. The transistor Q14 is cut off, and the signal at the output terminal OUT drops from "1" to "0". See the waveform F in Fig. 4.

When the base voltage of the transistor Q3 exceeds the voltage V_0 , the transistor Q3 is turned

on, the transistor Q4 is cut off, and the transistors Q5, Q6 and Q7 are cut off. As the result of turning on the transistor Q3, the capacitor C1 thus far being charged is discharged through the transistor Q3 to the ground potential V_{SS} . The base voltage of the transistor Q3 is immediately placed at the potential V_{SS} . See the waveform E in Fig. 4. Under this condition, the transistor Q1 is cut off, while the transistors Q2, Q8 and Q15 are turned on.

As the result of the cut-off of the transistor Q7, the base voltage of each of the transistors Q2, Q8 and Q15 becomes "1" in level, restoring the initial state of the burst gate pulse generating circuit. See the waveform B in Fig. 4.

Thus, for a normal sync separation pulse, a burst gate pulse of a fixed pulse width appears at a position delayed by a predetermined time behind the normal sync pulse.

As seen from the waveform A in Fig. 4, when noise is contained in the sync separation signal and the signal (depicted as a narrow pulse) rises due to the noise, the transistor Q1 is turned on and the transistor Q2 is cut off, as in case that a normal sync separation pulse is inputted. Accordingly, the charge to the capacitor C1 starts through the resistor R3, and the base voltage of the transistor Q3 starts to rise. See the waveform E in Fig. 4. When the noise pulse drops to "0" level, the transistor Q17 that has been turned on by the noise, is cut off. At this time, the collector voltage of the transistor Q2, or the charge voltage across the capacitor C1 (voltage V4 in the waveform E of Fig. 4), does not yet reach the voltage of the constant voltage source V3. Under this condition, after the transistor Q17 is turned off, the transistor Q19 is turned on. The turning on of the transistor Q19 turns on the transistor Q18 and turns off the transistor Q7. As a result, the transistor Q2 is turned on, and the capacitor C1 thus far being charged is discharged through the on-state transistor Q1. The base voltage of the transistor Q3 drops to a "0" level. See the waveform E in Fig. 4. Consequently, no further burst gate pulse is produced at the output terminal OUT.

To prevent the burst gate pulse from being mistakenly generated due to the noise contained in the sync separation signal, the voltage value of the constant voltage source V3 must be smaller than the voltage V5 (see the waveform E) that is obtained when the capacitor C1 is charged by the power source potential V_{CC} prior to a period T before a normal sync separation pulse arrives at the input terminal INPUT. The period T is equal to the pulse of the input sync separation pulse.

Claims

1. A burst gate pulse generating circuit compris-

ing:

first circuit means (10) for generating a first voltage increasing at a predetermined time constant in synchronism with the leading edge of a pulse contained in a sync signal applied thereto;

second circuit means (20) for stopping the first voltage generating operation by said first circuit means (10) when the trailing edge of said pulse contained in said sync signal arrives at said first circuit means (10) before said first voltage reaches a fixed second voltage; and

third circuit means (30) for generating a train of burst gate pulses through the comparison of said first voltage derived from said first circuit means (10) with fixed second and third voltages which are larger than said second voltage, and different from each other.

2. The burst gate pulse generating circuit according to claim 1, characterized in that said first circuit means (10) includes an input terminal (IN) for receiving said sync signal, a first transistor (Q2) whose conduction is controlled by the signal supplied to said input terminal (IN), a capacitor (C1) connected across the collector-emitter path of said first transistor (Q2), and a first resistor (R3) connected to a first end of said capacitor (C1) and a power source potential (V_{CC}).
3. The burst gate pulse generating circuit according to claim 1, characterized in that said second circuit means (20) includes voltage generating means (R6, R7, R4) for generating a fixed fifth voltage larger than said second, third and fourth voltages, first voltage comparing means (A1, Q5, R4, R5, R8) for comparing said first voltage with said fifth voltage, second voltage comparing means (A4, Q21, R14, R15) for comparing said first voltage with said second voltage, first control means (Q17, R16, R17) for controlling the voltage comparing means of said second voltage comparing means (A4, Q21) in accordance with said sync signal, and second control means (Q6, Q7, Q8, Q18, R9, R10) for controlling the voltage generating operation of said voltage generating means (R6, R7, R4) on the basis of the comparison result by said second voltage comparing means (A4, Q21).
4. The burst gate pulse generating circuit according to claim 3, characterized in that said voltage generating means (R6, R7, R4) includes second to fourth resistors (R6, R7, R4) inserted in series between the power source potential (V_{CC}) and ground potential (V_{SS}).



on, the transistor Q4 is cut off, and the transistors Q5, Q6 and Q7 are cut off. As the result of turning on the transistor Q3, the capacitor C1 thus far being charged is discharged through the transistor Q3 to the ground potential V_{SS} . The base-voltage of the transistor Q3 is immediately placed at the potential V_{SS} . See the waveform E in Fig. 4. Under this condition, the transistor Q1 is cut off, while the transistors Q2, Q8 and Q15 are turned on.

As the result of the cut-off of the transistor Q7, the base voltage of each of the transistors Q2, Q8 and Q15 becomes "1" in level, restoring the initial state of the burst gate pulse generating circuit. See the waveform B in Fig. 4.

Thus, for a normal sync separation pulse, a burst gate pulse of a fixed pulse width appears at a position delayed by a predetermined time behind the normal sync pulse.

As seen from the waveform A in Fig. 4, when noise is contained in the sync separation signal and the signal (depicted as a narrow pulse) rises due to the noise, the transistor Q1 is turned on and the transistor Q2 is cut off, as in case that a normal sync separation pulse is inputted. Accordingly, the charge to the capacitor C1 starts through the resistor R3, and the base voltage of the transistor Q3 starts to rise. See the waveform E in Fig. 4. When the noise pulse drops to "0" level, the transistor Q17 that has been turned on by the noise, is cut off. At this time, the collector voltage of the transistor Q2, or the charge voltage across the capacitor C1 (voltage V4 in the waveform E of Fig. 4), does not yet reach the voltage of the constant voltage source V3. Under this condition, after the transistor Q17 is turned off, the transistor Q19 is turned on. The turning on of the transistor Q19 turns on the transistor Q18 and turns off the transistor Q7. As a result, the transistor Q2 is turned on, and the capacitor C1 thus far being charged is discharged through the on-state transistor Q1. The base voltage of the transistor Q3 drops to a "0" level. See the waveform E in Fig. 4. Consequently, no further burst gate pulse is produced at the output terminal OUT.

To prevent the burst gate pulse from being mistakenly generated due to the noise contained in the sync separation signal, the voltage value of the constant voltage source V3 must be smaller than the voltage V5 (see the waveform E) that is obtained when the capacitor C1 is charged by the power source potential V_{CC} prior to a period T before a normal sync separation pulse arrives at the input terminal INPUT. The period T is equal to the pulse of the input sync separation pulse.

Claims

1. A burst gate pulse generating circuit compris-

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first circuit means (10) for generating a first voltage increasing at a predetermined time constant in synchronism with the leading edge of a pulse contained in a sync signal applied thereto;

second circuit means (20) for stopping the first voltage generating operation by said first circuit means (10) when the trailing edge of said pulse contained in said sync signal arrives at said first circuit means (10) before said first voltage reaches a fixed second voltage; and

third circuit means (30) for generating a train of burst gate pulses through the comparison of said first voltage derived from said first circuit means (10) with fixed second and third voltages which are larger than said second voltage, and different from each other.

2. The burst gate pulse generating circuit according to claim 1, characterized in that said first circuit means (10) includes an input terminal (IN) for receiving said sync signal, a first transistor (Q2) whose conduction is controlled by the signal supplied to said input terminal (IN), a capacitor (C1) connected across the collector-emitter path of said first transistor (Q2), and a first resistor (R3) connected to a first end of said capacitor (C1) and a power source potential (V_{CC}).
3. The burst gate pulse generating circuit according to claim 1, characterized in that said second circuit means (20) includes voltage generating means (R6, R7, R4) for generating a fixed fifth voltage larger than said second, third and fourth voltages, first voltage comparing means (A1, Q5, R4, R5, R8) for comparing said first voltage with said fifth voltage, second voltage comparing means (A4, Q21, R14, R15) for comparing said first voltage with said second voltage, first control means (Q17, R16, R17) for controlling the voltage comparing means of said second voltage comparing means (A4, Q21) in accordance with said sync signal, and second control means (Q6, Q7, Q8, Q18, R9, R10) for controlling the voltage generating operation of said voltage generating means (R6, R7, R4) on the basis of the comparison result by said second voltage comparing means (A4, Q21).
4. The burst gate pulse generating circuit according to claim 3, characterized in that said voltage generating means (R6, R7, R4) includes second to fourth resistors (R6, R7, R4) inserted in series between the power source potential (V_{CC}) and ground potential (V_{SS}).



5. The burst gate pulse generating circuit according to claim 3, characterized in that said first voltage comparing means (A1, Q, R4, R5, R8) includes a first differential amplifier (A1) made up of second and third transistors (Q3, Q4) of the npn type which are interconnected at the emitters and supplied with said first and fifth voltages, a fifth resistor (R5) connected between the ground potential (V_{ss}) and the interconnected emitters of said second and third transistors in said first differential amplifier (A1), said fourth resistor (R4) connected between the power source potential (V_{cc}) and the collector of said second transistor (Q3) in said first differential amplifier (A1), a sixth resistor (R8) connected at a first terminal to the power source potential (V_{cc}), and a fourth transistor (Q5) of the pnp type whose collector and base are connected to the collector of said third transistor (Q4), and whose emitter is connected to a second terminal of said sixth resistor (R8).

6. The burst gate pulse generating circuit according to claim 3, characterized in that said second voltage comparing means (A4, Q21, R14, R1) includes a second differential amplifier (A4) made up of fifth and sixth transistors (Q19, Q20) of the pnp type which are interconnected at the emitters and supplied with said first and fifth voltages, a seventh transistor (Q21) of the pnp type whose collector is connected to the interconnected emitters of said fifth and sixth transistors (Q19, Q20) in said second differential amplifier (A4), and whose base is coupled with the output of said first voltage comparing means (A1, Q5, R4, R, R8), a seventh resistor (R1) connected between the power source potential (V_{cc}) and the emitter of said seventh transistor (Q21), an eighth resistor (R14) connected between the collector of said fifth transistor (Q19) in said second differential amplifier (A4) and the ground potential.

7. The burst gate pulse generating circuit according to claim 3, characterized in that said first control means (Q17, R16, R17) includes an eighth transistor (Q17) of the npn type whose base is coupled for reception with said sync signal, emitter is coupled with the ground voltage, and the collector is coupled for transmission with said second voltage comparing means (A4, Q21).

8. The burst gate pulse generating circuit according to claim 3, characterized in that said second control means (Q6, Q7, Q8, Q18, R9, R10) includes a ninth transistor (Q18) whose base is coupled for reception with the output of said

second voltage comparing means and emitter is coupled with the ground voltage, a tenth transistor (Q6) whose base is coupled with the collector said ninth transistor (Q18), and whose base is coupled with the output of said first voltage comparing means (A1, Q5, R4, R5, R8), a ninth resistor (R9) connected between the emitter of said tenth transistor (Q6) and the power source potential (V_{cc}), a tenth resistor (R10) connected between the collector of said ninth transistor (Q18) and the ground voltage, an 11th transistor (Q7) of the npn type whose base is connected to the collector of said ninth transistor (Q18) and whose emitter is connected to the ground voltage, and a 12th transistor (Q8) when base is connected to the collector of said 10th transistor (Q18), emitter is connected to the ground voltage, and collector is connected to said voltage generating means (R6, R7, R4).

9. The burst gate pulse generating circuit according to claim 1, characterized in that said third circuit means (30) includes a third voltage comparing means (A2, Q11, R11, I2) for comparing said first voltage with said fourth voltage, a fourth voltage comparing means (A3, Q12, R12) for comparing said first voltage and said third voltage, a third control means (Q16) for controlling the voltage comparing operation of said third voltage comparing means (A2, Q11, R11, I2) in accordance with said sync signal, and a fourth control means (Q15) for controlling the voltage comparing operation by said fourth voltage comparing means (A3, Q12, R12) in accordance with said sync signal.

10. The burst gate pulse generating circuit according to claim 9, characterized in that said third voltage comparing means (A2, Q11, R11, I2) includes a third differential amplifier (A2) made up of 13th and 14th transistors (Q9, Q10) whose emitters are interconnected and supplied with said first and fourth voltages, a constant current source (I2) connected between the ground voltage and the interconnected emitters of said 13th and 14th transistors (Q9, Q10) in said third differential amplifier (A2), an 11th resistor (R11) connected at a first terminal to the power source potential (V_{cc}), and a 15th transistor (Q11) of the pnp type whose collector and base are connected to the collector of said 14th transistor (Q10) in said third differential amplifier (A2), and whose emitter is connected to a second terminal of said 11th resistor (R11).

11. The burst gate pulse generating circuit accord-



ing to claim 9, characterized in that said fourth voltage comparing means (A3, Q12, R12) includes a fourth differential amplifier (A3) made up of 16th and 17th transistors (Q13, Q14) whose emitters are interconnected and supplied with said first and third voltages, a 12th resistor (R12) connected at a first terminal to the power source potential (V_{CC}), and an 18th transistor (Q12) of the pnp type whose emitter is connected to a second terminal of said 12th resistor (R12), whose collector is connected to the interconnected emitters of said 16th and 17th transistors (Q13, Q14) in said fourth differential amplifier (A3), and whose base is coupled with the output of said third voltage comparing means (A2, Q11, R11, I2).

12. The burst gate pulse generating circuit according to claim 10, characterized in that said third control means (Q16) includes a 19th transistor (Q16) of the npn type whose collector is connected to the power source potential (V_{CC}), emitter is connected to the interconnected emitters of said 13th and 14th transistors (Q9, Q10) in said third differential amplifier (A2), and base is connected for reception with said sync signal.

13. The burst gate pulse generating circuit according to claim 11, characterized in that said fourth control means (Q15) includes a 20th transistor (Q15) of the npn type whose collector is connected to the interconnected emitter of said 16th transistor (Q13) in said fourth differential amplifier (A3), emitter is connected to the ground voltage, and whose base is coupled for reception with the inversion of said sync signal.

Patentansprüche

1. Burst-Torimpuls-Erzeugungsschaltung mit:

einer ersten Schaltungseinrichtung (10) zur Erzeugung einer ersten Spannung, die mit einer vorbestimmten Zeitkonstante synchron zur Vorderflanke eines Impulses zunimmt, der in einem an die Schaltung angelegten Synchronisierungssignal enthalten ist;

einer zweiten Schaltungseinrichtung (20) zum Anhalten des ersten Spannungserzeugungsvorgangs durch die erste Schaltungseinrichtung (10), wenn die Hinterflanke des in dem Synchronisierungssignal enthaltenen Impulses an der ersten Schaltungseinrichtung (10) ankommt, bevor die erste Spannung eine feste zweite Spannung erreicht; und

einer dritten Schaltungseinrichtung (30) zur Erzeugung eines Zuges von Burst-Torimpulsen durch den Vergleich der ersten Spannung, die von der ersten Schaltungseinrichtung (10) abgeleitet ist, mit festen zweiten und dritten Spannungen, die größer als die zweite Spannung und voneinander verschieden sind.

2. Burst-Torimpuls-Erzeugungsschaltung nach Anspruch 1, dadurch gekennzeichnet, daß die erste Schaltungseinrichtung (10) eine Eingangsklemme (IN) zum Empfang des Synchronisierungssignals aufweist, einen ersten Transistor (Q2), dessen Leitung durch das Signal gesteuert wird, welches der Eingangsklemme (IN) zugeführt wird, einen Kondensator (C1), der über den Kollektor-Emitter-Pfad des ersten Transistors (Q2) angeschlossen ist, und einen ersten Widerstand R3, der an ein erstes Ende des Kondensators (C1) und an ein Stromquellen-Potential (V_{CC}) angeschlossen ist.

3. Burst-Torimpuls-Erzeugungsschaltung nach Anspruch 1, dadurch gekennzeichnet, daß die zweite Schaltungseinrichtung (20) eine Spannungserzeugungseinrichtung (R6, R7, R4) aufweist, um eine feste fünfte Spannung zu erzeugen, die größer ist als die zweite, dritte und vierte Spannung, eine erste Spannungsvergleichseinrichtung (A1, Q5, R4, R5, R8) aufweist, um die erste Spannung mit der fünften Spannung zu vergleichen, eine zweite Spannungsvergleichseinrichtung (A4, Q2, R14, R15) zum Vergleich der ersten Spannung mit der zweiten Spannung, eine erste Steuereinrichtung (Q17, R16, R17), um die Spannungsvergleichseinrichtung der zweiten Spannungsvergleichseinrichtung (A4, Q21) entsprechend dem Synchronisierungssignal zu steuern, und eine zweite Steuereinrichtung (Q6, Q7, Q8, Q18, R9, R10), um den Spannungserzeugungsvorgang der Spannungserzeugungseinrichtung (R6, R7, R4) auf der Grundlage des Vergleichsergebnisses von der zweiten Spannungsvergleichseinrichtung (A4, Q21) zu steuern.

4. Burst-Torimpuls-Erzeugungsschaltung nach Anspruch 3, dadurch gekennzeichnet, daß die Spannungserzeugungseinrichtung (R6, R7, R4) einen zweiten bis vierten Widerstand (R6, R7, R4) aufweist, die in Reihe zwischen das Stromquellen-Potential (V_{CC}) und das Massepotential (V_{SS}) geschaltet sind.

5. Burst-Torimpuls-Erzeugungsschaltung nach Anspruch 3, dadurch gekennzeichnet, daß die



erste Spannungsvergleichseinrichtung (A1, Q, R4, R5, R8) einen ersten Differenzverstärker (A1) umfaßt, der aus einem zweiten und dritten Transistor (Q3, Q4) des npn-Typs besteht, wobei die Transistoren an den Emittern miteinander verbunden sind und mit der ersten und fünften Spannung versorgt werden, einen fünften Widerstand (R5), der zwischen das Massepotential (V_{ss}) und die miteinander verbundenen Emitter des zweiten und dritten Transistors in dem ersten Differenzverstärker (A1) geschaltet ist, wobei der vierte Widerstand (R4) zwischen das Stromquellen-Potential (V_{cc}) und den Kollektor des zweiten Transistors (Q3) in dem ersten Differenzverstärker (A1) geschaltet ist, einen sechsten Widerstand (R8), der an einer ersten Klemme mit dem Stromquellen-Potential (V_{cc}) verbunden ist, und einen vierten Transistor (Q5) des pnp-Typs, dessen Kollektor und Basis an den Kollektor des dritten Transistors (Q4) angeschlossen ist, und dessen Emitter mit einer zweiten Klemme des sechsten Widerstands (R8) verbunden ist.

6. Burst-Torimpuls-Erzeugungsschaltung nach Anspruch 3, dadurch gekennzeichnet, daß die zweite Spannungsvergleichseinrichtung (A4, Q21, R14, R1) einen zweiten Differenzverstärker (A4) umfaßt, der aus einem fünften und sechsten Transistor (Q19, Q20) des pnp-Typs besteht, wobei die Transistoren an den Emittern miteinander verbunden sind und mit der ersten und fünften Spannung versorgt werden, einem siebten Transistor (Q21) des pnp-Typs, dessen Kollektor an die miteinander verbundenen Emitter des fünften und sechsten Transistors (Q19, Q20) in dem zweiten Differenzverstärker (A4) angeschlossen ist, und dessen Basis mit dem Ausgang der ersten Spannungsvergleichseinrichtung (A1, Q5, R4, R, R8) verbunden ist, einem siebten Widerstand (R1), der zwischen das Stromquellen-Potential (V_{cc}) und den Emitter des siebten Transistors (Q21) geschaltet ist, und einem achten Widerstand (R14), der zwischen den Kollektor des fünften Transistors (Q19) in dem zweiten Differenzverstärker (A4) und das Massepotential geschaltet ist.

7. Burst-Torimpuls-Erzeugungsschaltung nach Anspruch 3, dadurch gekennzeichnet, daß die erste Steuereinrichtung (A17, R16, R17) einen achten Transistor (Q17) des npn-Typs aufweist, dessen Basis zum Empfang des Synchronisierungssignals angeschlossen ist, dessen Emitter an die Massespannung angeschlossen ist, und dessen Kollektor zur Übertragung an die zweite Spannungsvergleichsein-

richtung (A4, Q21) angeschlossen ist.

8. Burst-Torimpuls-Erzeugungsschaltung nach Anspruch 3, dadurch gekennzeichnet, daß die zweite Steuereinrichtung (Q6, Q7, Q8, Q18, R9, R10) einen neunten Transistor (Q18) umfaßt, dessen Basis zum Empfang des Ausgangssignals der zweiten Spannungsvergleichseinrichtung und dessen Emitter an die Massespannung angeschlossen ist, einen zehnten Transistor (Q6), dessen Basis an den Kollektor des neunten Transistors (Q18) angeschlossen ist, und dessen Basis an den Ausgang der ersten Spannungsvergleichseinrichtung (A1, Q5, R4, R5, R8) angeschlossen ist, einen zwischen den Emitter des zehnten Transistor (Q6) und das Stromquellen-Potential (V_{cc}) geschalteten neunten Widerstand (R9), einen zwischen den Kollektor des neunten Transistors (Q18) und die Massespannung geschalteten zehnten Widerstand (R10), einen elften Transistor (Q7) des npn-Typs, dessen Basis an den Kollektor des neunten Transistors (Q18) und dessen Emitter an die Massespannung angeschlossen ist, und einen zwölften Transistor (Q8), dessen Basis an den Kollektor des zehnten Transistors (Q18) angeschlossen ist, dessen Emitter mit der Massespannung verbunden ist, und dessen Kollektor mit der Spannungserzeugungseinrichtung (R6, R7, R4) verbunden ist.

9. Burst-Torimpuls-Erzeugungsschaltung nach Anspruch 1, dadurch gekennzeichnet, daß die dritte Schaltungseinrichtung (30) eine dritte Spannungsvergleichseinrichtung (A2, Q11, R11, I2) aufweist, um die erste Spannung mit der vierten Spannung zu vergleichen, eine vierte Spannungsvergleichseinrichtung (A3, Q12, R12), um die erste Spannung und die dritte Spannung zu vergleichen, eine dritte Steuereinrichtung (Q16) zum Steuern des Spannungsvergleichsvorgangs der dritten Spannungsvergleichseinrichtung (A2, Q11, R11, I2) entsprechend dem Synchronisierungssignal, und eine vierte Steuereinrichtung (Q15) zum Steuern des Spannungsvergleichsvorgangs durch die vierte Spannungsvergleichseinrichtung (A3, Q12, R12) entsprechend dem Synchronisierungssignal.

10. Burst-Torimpuls-Erzeugungsschaltung nach Anspruch 9, dadurch gekennzeichnet, daß die dritte Spannungsvergleichseinrichtung (A2, Q11, R11, I2) einen dritten Differenzverstärker (A2) umfaßt, der aus einem dreizehnten und einem vierzehnten Transistor (Q9, Q10) besteht, deren Emitter miteinander verbunden



sind und mit der ersten und vierten Spannung versorgt werden, einer Konstant-Stromquelle (I2), die zwischen die Massespannung und die miteinander verbundenen Emitter des dreizehnten und vierzehnten Transistors (Q9, Q10) in dem dritten Differenzverstärker (A2) geschaltet ist, einem elften Widerstand (R11), der an einer ersten Klemme an das Stromquellen-Potential (V_{CC}) angeschlossen ist, und einem fünfzehnten Transistor (Q11) des pnp-Typs, dessen Kollektor und Basis an den Kollektor des vierzehnten Transistors (Q10) in dem dritten Differenzverstärker (A2) angeschlossen sind, und dessen Emitter an eine zweite Klemme des elften Widerstands (R11) angeschlossen ist.

11. Burst-Torimpuls-Erzeugungsschaltung nach Anspruch 9, dadurch gekennzeichnet, daß die vierte Spannungsvergleichseinrichtung (A3, Q12, R12) einen vierten Differenzverstärker (A3) umfaßt, der aus einem sechzehnten und siebzehnten Transistor (Q13, Q14) besteht, deren Emitter miteinander verbunden sind und mit der ersten und dritten Spannung versorgt werden, einem zwölften Widerstand (R12), der an einer ersten Klemme an das Stromquellen-Potential (V_{CC}) angeschlossen ist, und einem achtzehnten Transistor (Q12) des pnp-Typs, dessen Emitter an eine zweite Klemme des zwölften Widerstands (R12) angeschlossen ist, dessen Kollektor mit den miteinander verbundenen Emittoren des sechzehnten und siebzehnten Transistors (Q13, Q14) in dem vierten Differenzverstärker (A3) verbunden ist, und dessen Basis an den Ausgang der dritten Spannungsvergleichseinrichtung (A2, Q11, R11, I2) angeschlossen ist.

12. Burst-Torimpuls-Erzeugungsschaltung nach Anspruch 10, dadurch gekennzeichnet, daß die dritte Steuereinrichtung (Q16) einen neunzehnten Transistor (Q16) des npn-Typs aufweist, dessen Kollektor an das Stromquellen-Potential (V_{CC}) angeschlossen ist, dessen Emitter an die miteinander verbundenen Emitter des dreizehnten und vierzehnten Transistors (Q9, Q10) in dem dritten Differenzverstärker (A2) angeschlossen ist, und dessen Basis für den Empfang des Synchronisierungssignals angeschlossen ist.

13. Burst-Torimpuls-Erzeugungsschaltung nach Anspruch 11, dadurch gekennzeichnet, daß die vierte Steuereinrichtung (Q15) einen zwanzigsten Transistor (Q15) des npn-Typs umfaßt, dessen Kollektor mit dem verbundenen Emitter des sechzehnten Transistors (Q13) in dem

vierten Referenzverstärker (A3) verbunden ist, dessen Emitter an die Massespannung angeschlossen ist, und dessen Basis zum Empfang des invertierten Synchronisierungssignals angeschlossen ist.

Revendications

1. Circuit de génération d'impulsion de commande de burst comprenant :

un premier moyen de circuit (10) pour générer une première tension qui augmente selon une constante de temps prédéterminé en synchronisation avec le front avant d'une impulsion contenue dans un signal de synchronisation qui lui est appliqué ;

un second moyen de circuit (20) pour arrêter la première opération de génération de tension due audit premier moyen de circuit (10) lorsque le front arrière de ladite impulsion contenue dans ledit signal de synchronisation arrive audit premier moyen de circuit (10) avant que ladite première tension n'atteigne une seconde tension fixe ; et

un troisième moyen de circuit (30) pour générer un train d'impulsions de commande de burst par l'intermédiaire de la comparaison de ladite première tension dérivée dudit premier moyen de circuit (10) à des seconde et troisième tensions fixes qui sont plus importantes que ladite seconde tension et qui sont différentes l'une de l'autre.

2. Circuit de génération d'impulsion de commande de burst selon la revendication 1, caractérisé en ce que ledit premier moyen de circuit (10) inclut une borne d'entrée (IN) pour recevoir ledit signal de synchronisation, un premier transistor (Q2) dont la conduction est commandée par le signal appliqué à ladite borne d'entrée (IN), une capacité (C1) connectée aux bornes de la voie collecteur-émetteur dudit premier transistor (Q2) et une première résistance (R3) connectée à une première extrémité de ladite capacité (C1) ainsi qu'à un potentiel de source d'alimentation (V_{CC}).

3. Circuit de génération d'impulsion de commande de burst selon la revendication 1, caractérisé en ce que ledit second moyen de circuit (20) inclut un moyen de génération de tension (R6, R7, R4) pour générer une cinquième tension fixe plus importante que lesdites seconde, troisième et quatrième tensions, un premier moyen de comparaison de tension (A1, Q5, R4, R5, R8) pour comparer ladite première tension à ladite cinquième tension, un second moyen de comparaison de tension (A4, Q21,



R14, R15) pour comparer ladite première tension à ladite seconde tension, un premier moyen de commande (Q17, R16, R17) pour commander le moyen de comparaison de tension (A4, Q21) en relation avec ledit signal de synchronisation et un second moyen de commande (Q6, Q7, Q8, Q18, R9, R10) pour commander l'opération de génération de tension dudit moyen de génération de tension (R6, R7, R4) sur la base du résultat de comparaison délivré par ledit second moyen de comparaison de tension (A4, Q21).

4. Circuit de génération d'impulsion de commande de burst selon la revendication 3, caractérisé en ce que ledit moyen de génération de tension (R6, R7, R4) inclut des second à quatrième transistors (R6, R7, R4) insérés en série entre le potentiel de source d'alimentation (V_{CC}) et un potentiel de masse (V_{SS}).

5. Circuit de génération d'impulsion de commande de burst selon la revendication 3, caractérisé en ce que ledit premier moyen de comparaison de tension (A1, Q5, R4, R5, R8) inclut un premier amplificateur différentiel (A1) constitué par des second et troisième transistors (Q3, Q4) du type NPN qui sont interconnectés au niveau des émetteurs et qui se voient appliquer lesdites première et cinquième tensions, par une cinquième résistance (R5) connectée entre le potentiel de la masse (V_{SS}) et les émetteurs interconnectés desdits second et troisième transistors contenus dans ledit premier amplificateur différentiel (A1), par ladite quatrième résistance (R4) connectée entre le potentiel de source d'alimentation (V_{CC}) et le collecteur dudit second transistor (Q3) contenu dans ledit premier amplificateur différentiel (A1), par une sixième résistance (R8) connectée au niveau d'une première borne au potentiel de source d'alimentation (V_{CC}) et par un quatrième transistor (Q5) du type PNP dont le collecteur et la base sont connectés au collecteur dudit troisième transistor (Q4) et dont l'émetteur est connecté à une seconde borne de ladite sixième résistance (R8).

6. Circuit de génération d'impulsion de commande de burst selon la revendication 3, caractérisé en ce que ledit second moyen de comparaison de tension (A4, Q21, R14, R1) inclut un second amplificateur différentiel (A4) constitué par des cinquième et sixième transistors (Q19, Q20) du type PNP qui sont interconnectés au niveau des émetteurs et qui se voient appliquer lesdites première et cinquième tensions,

par un septième transistor (Q21) du type PNP dont le collecteur est connecté aux émetteurs interconnectés desdits cinquième et sixième transistors (Q19, Q20) contenus dans ledit second amplificateur différentiel (A4) et dont la base est couplée à la sortie dudit premier moyen de comparaison de tension (A1, Q5, R4, R5, R8), par une septième résistance (R1) connectée entre le potentiel de source d'alimentation (V_{CC}) et l'émetteur dudit septième transistor (Q21) et par une huitième résistance (R14) connectée entre le collecteur dudit cinquième transistor (Q19) contenu dans ledit second amplificateur différentiel (A4) et le potentiel de la masse.

7. Circuit de génération d'impulsion de commande de burst selon la revendication 3, caractérisé en ce que ledit premier moyen de commande (Q17, R16, R17) inclut un huitième transistor (Q17) du type NPN dont la base est couplée pour la réception audit signal de synchronisation, dont l'émetteur est couplé à la tension de masse et dont le collecteur est couplé pour la transmission audit second moyen de comparaison de tension (A4, Q21).

8. Circuit de génération d'impulsion de commande de burst selon la revendication 3, caractérisé en ce que ledit second moyen de commande (Q6, Q7, Q8, Q18, R9, R10) inclut un neuvième transistor (Q18) dont la base est couplée pour la réception à la sortie dudit second moyen de comparaison de tension et dont l'émetteur est couplé à la tension de masse, un dixième transistor (Q6) dont le collecteur est couplé au collecteur dudit neuvième transistor (Q18) et dont la base est couplée à la sortie dudit premier moyen de comparaison de tension (A1, Q5, R4, R5, R8), une neuvième résistance (R9) connectée entre l'émetteur dudit dixième transistor (Q6) et le potentiel de source d'alimentation (V_{CC}), une dixième résistance (R10) connectée entre le collecteur dudit neuvième transistor (Q18) et la tension de masse, un onzième transistor (Q7) du type NPN dont la base est connectée au collecteur dudit neuvième transistor (Q18) et dont l'émetteur est connecté à la tension de masse et un douzième transistor (Q8) dont la base est connectée au collecteur dudit dixième transistor (Q18), dont l'émetteur est connecté à la tension de masse et dont le collecteur est connecté audit moyen de génération de tension (R6, R7, R4).

9. Circuit de génération d'impulsion de commande de burst selon la revendication 1, caractérisé



- se en ce que ledit troisième moyen de circuit (30) inclut un troisième moyen de comparaison de tension (A2, Q11, R11, I2) pour comparer ladite première tension à ladite quatrième tension, un quatrième moyen de comparaison de tension (A3, Q12, R12) pour comparer ladite première tension à ladite troisième tension, un troisième moyen de commande (Q16) pour commander l'opération de comparaison de tension dudit troisième moyen de comparaison de tension (A2, Q11, R11, I2) en relation avec ledit signal de synchronisation et un quatrième moyen de commande (Q15) pour commander l'opération de comparaison de tension effectuée par ledit quatrième moyen de comparaison de tension (A3, Q12, R12) en relation avec ledit signal de synchronisation.
10. Circuit de génération d'impulsion de commande de burst selon la revendication 9, caractérisé en ce que ledit troisième moyen de comparaison de tension (A2, Q11, R11, I2) inclut un troisième amplificateur différentiel (A2) constitué par des treizième et quatorzième transistors (Q9, Q10) dont les émetteurs sont interconnectés et qui se voient appliquer lesdites première et quatrième tensions, par une source de courant constant (I2) connectée entre la tension de masse et les émetteurs interconnectés desdits treizième et quatorzième transistors (Q9, Q10) contenus dans ledit troisième amplificateur différentiel (A2), par une onzième résistance (R11) connectée au niveau d'une première borne au potentiel de source d'alimentation (V_{CC}) et par un quinzième transistor (Q11) du type PNP dont le collecteur et la base sont connectés au collecteur dudit quatorzième transistor (Q10) contenu dans ledit troisième amplificateur différentiel (A2) et dont l'émetteur est connecté à une seconde borne de ladite onzième résistance (R11).
11. Circuit de génération d'impulsion de commande de burst selon la revendication 9, caractérisé en ce que ledit quatrième moyen de comparaison de tension (A3, Q12, R12) inclut un quatrième amplificateur différentiel (A3) constitué par des seizième et dix-septième transistors (Q13, Q14) dont les émetteurs sont interconnectés et qui se voient appliquer lesdites première et troisième tensions, par une douzième résistance (R12) connectée au niveau d'une première borne au potentiel de source d'alimentation (V_{CC}) et par un dix-huitième transistor (Q12) du type PNP dont l'émetteur est connecté à une seconde borne de ladite douzième résistance (R12), dont le collecteur est connecté aux émetteurs interconnectés desdits seizième et dix-septième transistors (Q13, Q14) contenus dans ledit quatrième amplificateur différentiel (A3) et dont la base est couplée à la sortie dudit troisième moyen de comparaison de tension (A2, Q11, R11, I2).
12. Circuit de génération d'impulsion de commande de burst selon la revendication 10, caractérisé en ce que ledit troisième moyen de commande (Q16) inclut un dix-neuvième transistor (Q16) du type NPN dont le collecteur est connecté au potentiel de source d'alimentation (V_{CC}), dont l'émetteur est connecté aux émetteurs interconnectés desdits treizième et quatorzième transistors (Q9, Q10) contenus dans ledit troisième amplificateur différentiel (A2) et dont la base est connectée pour la réception audit signal de synchronisation.
13. Circuit de génération d'impulsion de commande de burst selon la revendication 11, caractérisé en ce que ledit quatrième moyen de commande (Q15) inclut un vingtième transistor (Q15) du type NPN dont le collecteur est connecté à l'émetteur interconnecté dudit seizième transistor (Q13) contenu dans ledit quatrième amplificateur différentiel (A3), dont l'émetteur est connecté à la tension de masse et dont la base est couplée pour la réception à l'inversion dudit signal de synchronisation.